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CIA-RDP86-00513R000617320017-4
                "APPROVED FOR RELEASE: 09/19/2001
                                               Plent Diseases. Diseases of Force: Species
                COUNTRY
                ABS. JOUR. : RZhBiol., No. 23 1998, No. 104972
                CATEGORY
                                           Tutter Republic Scientific and Technical Society of
                                                   Fungus Diseases of Auerns in Middle Povolzh'ye and
                  AUTHOR
                                                    Measures for Their Control.
                  INST.
                                                    Sb. statey po les. kb-vu. Tatersk. resp. nauchn-tekhn.
                  TITLE
                                                    0-40 lear. prom-st1, 1956, vyr. 12, 159-208
                                                     A number of fungi has been discovered causing diseases in
                                                      the oak acorna in the suvironment of Middle Povolsh'ye.
                   onto. PUB.
                                                      The majority of them are assigned to the group of imper-
                                                       fact fungi; escomycetes, basidiomycetes and fungi-algae
                    ARST? ACT
                                                       are represented in smaller numbers. Fungi affecting the
                                                       oak acorns can develop on acorns remaining in the forest
                                                        from the crop of the previous year, on living branches,
                                                        leaves and trunks of the oak, on fallen leaves and dead
                                                           e) Lumber Industry
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       A-CTRACT
                                t word, on different kinds of organic matter out on differ-
                                   Committees favoring the canalognant of timenans in accome
                                   ore instrated. Oak ecorns were tropied with preparetion
                                  Militer 2 Standson ethylamicorporlibride), with Matherial
                                  of the standard of the standar
                                 Many The best results were obtained with AMIS-2 (at
                                the rate of 1.5 grams/kg of the asses). Along with the
                                Emploided treatment of the scorne, prophylactic seasons
                               are recommended having as their purpose the prevention of
                              their affection during Rathering, resulting, transportation
CARD: 2/2
                              anc storage. - A. A. Frinyezhayuk
                    GULYAYEV V.V.
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                      of the Y
                                               : Flant Dispases. Forest Trees.
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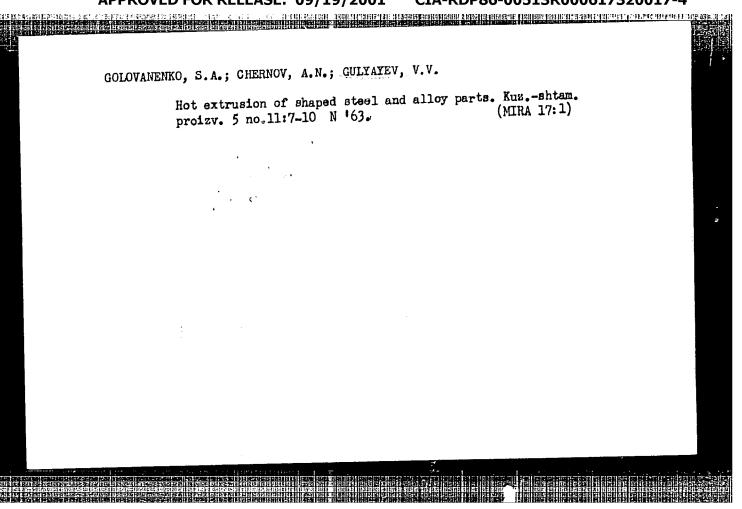
GOLOVANENKO, S.A.; CHERNOV, A.N.; SAPOZHNIKOV, V.M.; SINITSYN, V.G.;

GULYAYEV, V.V.

Extrusion of bimetal shapes. Kuz.-shtam. proizv. 5 no.10:

7-9 0 '63.

(MIRA 16:11)



ACCESSION NR: AP4019027

S/0182/64/000/002/0045/0047

AUTHORS: Grishkov, A. I.; Chernov, A. N.; Gulyayev, V. V.

TITLE: Pressure indicator for high speed hydraulic presses

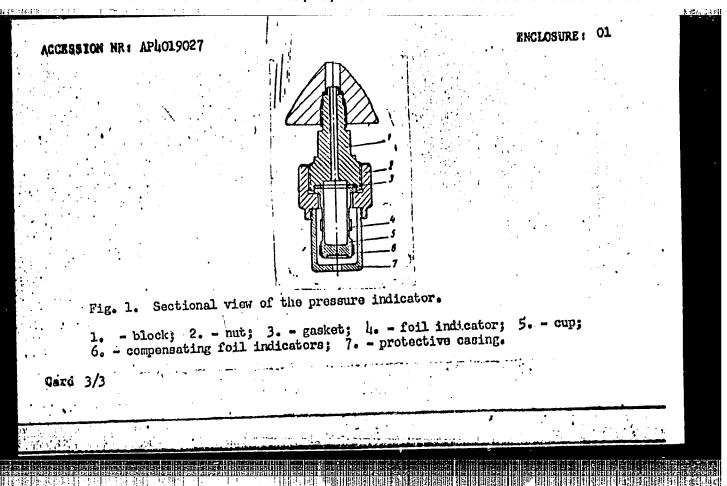
SOURCE: Kuznechno-shtampovochnoye proizvodstvo, no. 2, 1964, 45-47

TOPIC TAGS: hydraulic press, pressure indicator, stamping, manometer, recording manometer, foil indicator

ABSTRACT: A pressure indicator was designed by TsNIIChM for measuring the force applied and the pressing velocity in the 150-ton hydraulic press P6648 used for hot stamping of ferrous metals and alloys at up to 300 mm/sec. The working principle of the indicator is based on the variation in the elastic deformation of a thin-walled container under the action of the internal pressure of the liquid inflowing from the main cylinder of the hydraulic press. The pressure indicator (see Fig. 1 of the Enclosure) consisted of a block (1) and a cup (5) with thin elastic walls and a rigid bottom. The cup is attached to (1) by the nut (2). Two foil indicators (4) are fixed to the thin wall and two (6) to the rigid bottom of the cup. All the indicators are lacquored and covered with lacquer-saturated

Card 1/3

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casing(7). T device itself	is simpl	.e, compact,	and stable.	It can be	used for mea	suring	i
pressures in Orig. art. ha			chanisms with	i working spe	eeds up to 30	00-400 mm/sec.	i
ASSOCIATION 8	none.	•		•		•	:
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Card 2/3						•	



CHERNOV, A.E.; GULYAYEV, V.V.

Method of determining the adhesive strength of layers in round bimetallic profiles. Zav. lab. 30 no.11:1394 164 (MIRA 18:1)

1. TSentral'nyy nauchno-issledovatel'skiy institut chernoy metallurgii im. I.P. Bardina.

	्या वस्त्राम्यागनमास्त
L 36139-66 EWP(e)/EWT(m)/EWP(v)/T/EWP(t)/ETI/EWP(k)	1/2
AUTHOR: Chernov, A. N.; Golovanenko, S. A.; Gulyayev, V. V.	10
ORG: none	•
TITLE: Features of the fabrication of bimetal shapes by the hot pressing method	
SOURCE: Moscow. Tsentral'nyy nauchno- issledovatel'skiy institut chernoy metalium gii. Sbornik frudov, no. 42, 1965, Proizvodstvo bimetallov (Production of bimetallov)	r- s),
92-100 TOPIC TAGS: chromium steel, nickel steel, bimetal, metal extrusion, metal pressi Kh18N9I steel, St. 3 steel	ng /
ABSTRACT: The article describes the experimental study of the hot pressing of bishapes performed at the Scientific Research Institute of Ferrous Metallurgy in 19. The technique employed was that of direct extrusion, in an 800-ton vertical hydrau press, from a container with an inside diameter of 80 mm. Rods measuring 50-25 mm diameter, with various thickness of cladding layer, were thus produced from such diameter, with various thickness of cladding layer, were thus produced from such	lic n in
dismeter, with various thickness of clauding layer, which was the clause materials as, chiefly, St. 3 steel as the core and Khl8N9T Ni-Cr steel as the clause ding sheath. The extrusion was performed on using a container heated to 400°C and die heated to 250-300°C. The pattern of distribution of the cladding layer along length of the bimetal rods was investigated by comparing the variation in the cro	i a the
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L 36139-66 ACC NR: AT6016765

-sectional area of the base-metal core under various conditions of extrusion and correlating it with the formulas for the volumetric content of the cladding and base materials. It was thus found that the flow pattern of metal through the die hole is a major factor in determining the lengthwise pattern of distribution of the cladding sheath and hence also the geometry of the base-metal core; it can be optimized by retarding the flow of the core metal during the initial stage of extrusion. In view of the considerable advantages of the hot pressing of bimetal shapes as compared with their hot and cold rolling, it is expedient to organize this pressing on an industrial scale. This will make it possible to: 1) expand the current variety of bimetals; 2) obtain bimetal shapes with various combinations of metals, as well as with intricately shaped cross sections which cannot be obtained by rolling; 3) produce small lots of bimetal shapes at lower cost compared with rolling: 4) reduce by 40-50% the unit consumption of expensive and scarce metals and alloys. Orig. art. has: 6 figures, 1 table, 2 formulas.

SUB CODE: 13, 11/ SUBM DATE: none/ ORIG REF: 005

Sheath Rolling 1

Joining of Dissimilar Metals (

Card 2/2 //

医锥状螺旋形 精育 经国际 美国人工会员

AUTHOR:	Chernov, A. I	1.; Golovaneni	ko, S. A.; Gulyaye	v, V. V.	101/0106 /// Br	
	one					
TITLE:	Investigation	of the bonding	ng strength of lay	ers in hot-press	ed bimetai	4.
SOURCE: Sbornik	Moscow. Tsen	tral'nyy nauc 2, 1965. Proi	hno-issledovatel's zvodstvo bimetallo	skiy institut che ov (Production of	bimetals), 101	-
); il steel, metal pro			
bimetal	l, metal claddi	ng / St. 3 at	eer, Kilonyr accan	_		l
ABSTRACE sence ation. torted connector bi	CT: By contrast the state of a uniform di As a result, de and the adhesition, the authometal rods of S	et with rolling ded together latribution of luring pressing lon (bonding) ors investigated at the latribute of the latribute	ng, during pressing simultaneously over the state of the strength of the stren	g the core and sher the entire corve stresses in the core remains viand sheath is great the adhesion of the produced by	ne area of defor Irtually undis- eater. In this f sheath to core hot pressing in were subjected	to
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L 36140-66

ACC NR: AT6016766

resistance depends not only on the degree of relative reduction in area but also on the content of the cladding layer. Thus, for rods of 25 mm diameter subjected to pressing with a 91% relative reduction in area, shear resistance increases with increase in volumetric content of cladding layer (Fig. 1). Reason: as the content of the

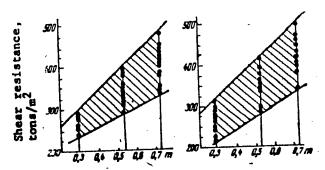


Fig. 1. Shear resistance as a function of volumetric content m of the cladding

a - during extrusion of core; b - during twisting

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L 36140-66 ACC NR: AT6016766

hard component increases, the pressure that must be exerted on the bimetal also increases and this, in its turn, contributes to increasing the adhesion between the layers. Adhesion strength is also markedly affected by such factors as the quality of surface treatment and the techniques of the assembling and welding of the original bimetal blanks. On the basis of these tests it may be concluded that the minimum required strength of the bonding between the layers, which for bimetal sheets of St. 3 and Kh18N9T steels amounts to 15 kg/mm², can be attained for rods with even a relatively thin cladding layer (m = 0.3) by applying a relative reduction area smounting to 70-80%, which corresponds to reduction by a factor of 3.3-5.0. As the volumetric content of the hard component (cladding material) increases from 0.3 to 0.7, bonding strength increases 1.3-1.4 times. Orig. art. has: 5 figures.

SUB CODE: 13, 11/ SUBM DATE: none/ ORIG REF: 002

Joining of Dissimilar Metals 19

Card 3/3 ///-

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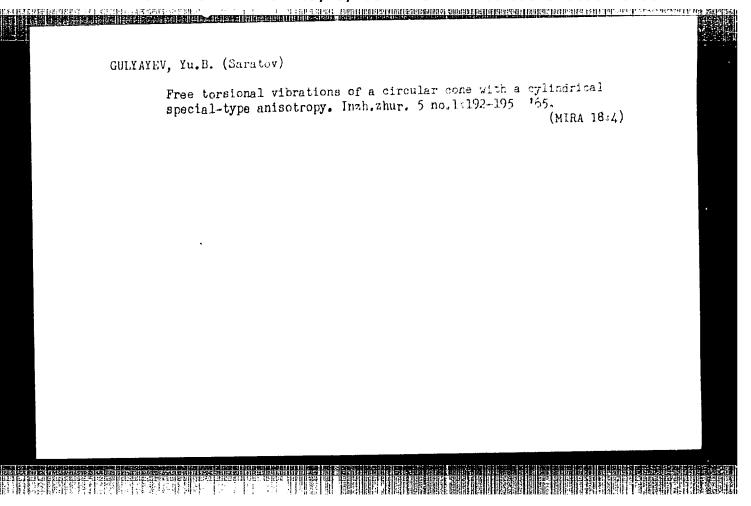
GULYAYEV, Ye.A.

Character of changes in the nonhemoglobin iron content of blood serum in lymphogranulomatosis. Probl. gemat. i perel. (MIRA 18:11) krovi no.2:36-37 '65.

1. Gospital'naya terapevticheskaya klinika (zav. - prof. A.I. Germanov) Kuybyshevskogo meditsinskogo instituta.

BLANK, E.M.; YUHOVSKIY, Yu.I.; GUIYAYEV, Yu.A., inzh., retsenzent; CHILIKINA, N.D., inzh., red.; STEFANCHENKO, N.S., red. izd-va; DEMKINA, N.F., tekhn. red.

[Handbook for mold makers] Spravochnik formovshchika. Moskva, Mashgiz, 1963. 182 p. (MIRA 17:2)



ALEKSEYEVA, V.G.; GULYAYEV, Yu.V.

Second All-Union Conference on Photoelectric and Optical Phenomena in Semiconductors. Radiotekh. 1 elektron. 7 no.4: (MIRA 15:3)

722 Ap '62. (Semiconductors—Congresses)

GULYAYEV, Yu.V.; PUSTGVOYT, V.1.

Amplification of surface waves in semiconductors. Zhur.eksp. i teor.fiz. 47 no.6:2251-2253 D '64. (MIRA 18:2)

1. Institut radiotekhniki i elektroniki AN SSSR i Institut fiziko-tekhnicheskikh i radiotekhnicheskikh izmereniy.

APPROVED FOR RELEASE: 09/19/2001 CIA-RDP86-00513R000617320017-4"

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	USSR/Miscellar	neous - Radio clubs						
	Card 1/1	Pub, 89 - 6/32						\$
	Authors :	Semenov, N., and Gulyaev, YA.						
	Title :	DOSAAF radio clubs and other organizations			3 			
		Radio 2, page 10, Feb 1955						
	Abstract :	The activities of the local radio club of the development of radio skill by radio amateurs problems related to radio communications, as	s and the	e discu	SSION OI	on.		1
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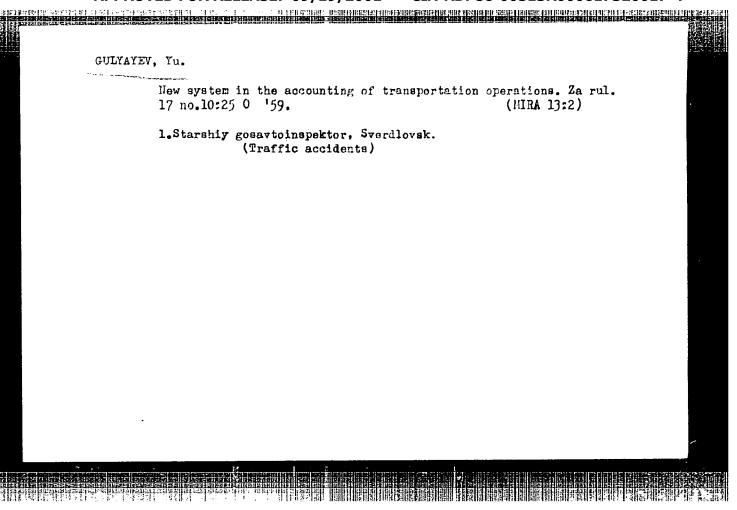
GULYAYEV, Ye.A.

Nonhemoglobin serum iron and total blood iron in normal subjects.

Terap.arkh. 31 no.11:65-69 N '59. (MIRA 13:3)

1. Iz gospital noy terapevticheskoy kliniki (zaveduyushchiy - prof.
A.I. Germanov) Kuybyshevskogo meditsinskogo instituta i Kuybyshevskoy
oblastnoy stantsii perelivaniya krovi (zaveduyushchiy M.F. Fedorovskaya).

(IRON blood)



GULYAYEV, Yu.F., starshiy tekhnik-leytenant

Flight preparation ourfit. Vest.Vozd.Fl. 41 no.2:60 F '59.

(MIRA 12:4)

(Airplanes--Maintenance and repair--Equipment and supplies)

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L 26124-66 EPF(n)-2/EWT(1)/ETC(m)-6

ACC NR: AP6015806 SOURCE CODE: UR/03/36/66/003/010/0410/0413

4 / 4 / 6

AUTHOR: Gulyayev, Yu. G.; Epshteyn, E. M.

ORG: Institute of Radio Engineering and Electronics, Academy of Sciences SSSR (Institut radiotekhniki i elektroniki Akademii nauk SSSR)

TITIE: Acousto-thermal effect in semiconductors

SOURCE: Zhurnal eksperimental'noy i teoreticheskoy fiziki. Pis'ma v redaktsiyu. Prilozheniye, v. 3, no. 10, 1966, 410-413

TOPIC TAGS: thermal acoustic effect, phonon drag, temperature gradient, semiconductor crystal

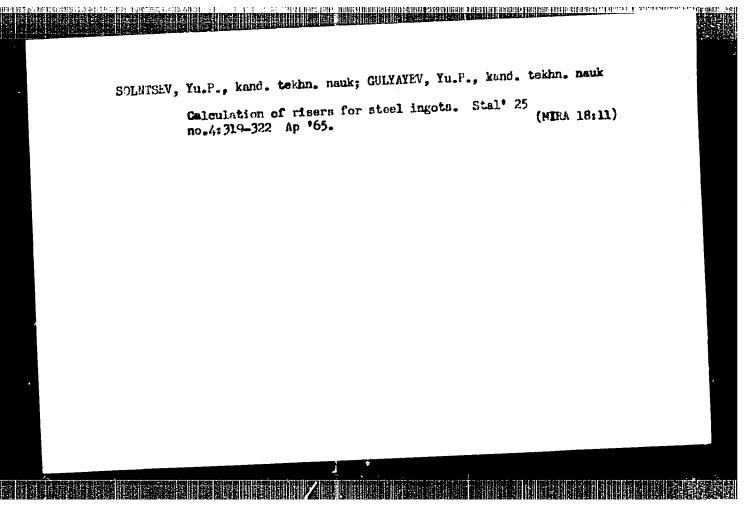
ABSTRACT: The authors show that excitation of a monochromatic flux of phonons in a crystal by an external source produces, besides the well known acousto-electric effect, also a temperature gradient under adiabatic conditions. In analogy with the acousto-electric effect, they call this phenomenon the acousto-thermal effect. The results of this effect are presented analytically for a non-piezoelectric crystal in which the carriers are characterized by an isotropic effective mass and a relaxation time that depend on the energy, and in which a hypersonic wave propagates. By regarding such a wave as a current of monochromatic phonons and by calculating the integral of the collisions between the electrons and the phonon current, the antisymmetrical part of the distribution function is obtained, from which the electric current density and the heat flux density are calculated. It is found that the effect

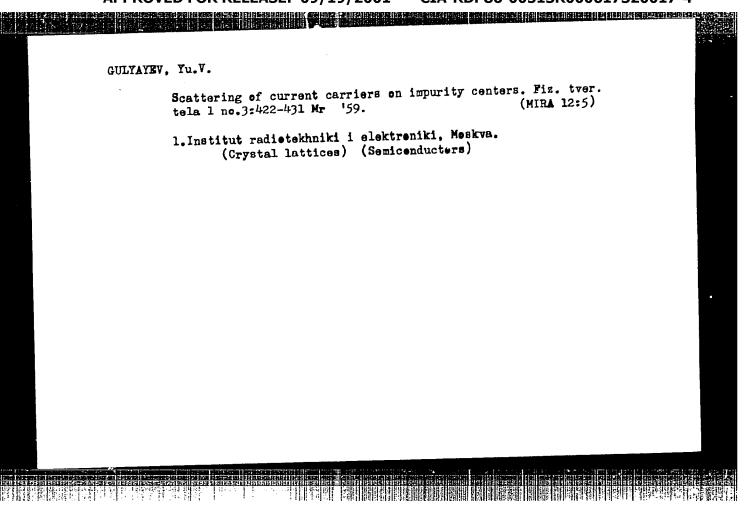
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1	L 40282-65 EVT(d)/EVT(m)/EVP(w)/EVA(d)/EVP(v)/EVP(k)/EVA(h) Pf-1/Peb EM ACCESSION NR: AP5006171 S/0258/65/005/001/0192/0195
	AUTHOR: Gulyayev, Yu. P. (Saratov)
	TITLE: Free torsional vibrations of a circular cone with cylindrical anisotropy of a particular kind
	SOURCE: Inzhenernyy zhurnal, v. 5, no. 1, 1965, 192-195
	TOPIC TAGS: torsional cone vibration, cone natural frequency, and sotropic cone vibration, orthotropic cone vibration
	ABSTRACT: The problem of determining the natural frequency of a circular cone possessing cylindrical anisotropy such that its axis coincides with the geometric axis of the cone and all its radial planes cides with the geometric axis of the cone and all its radial planes are elastic-symmetry planes is discussed. All points of the base of the cone are are elastic-symmetry planes is discussed that the cone cross sections are not rigidly fixed. It is assumed that the cone cross sections are not
	rigidly fixed. It is assumed that the cone cross section or radial disedistorted under torsional vibrations and that there are no radial diseplacements. The problem is reduced to an analogous one for an isoplacements. The problem is reduced to an analogous one for an isoplacements. The problem is reduced to an analogous one for an isoplacements. The problem of a different meridional cross section by means of a tropic cone with a different meridional cross section by means of a tropic cone with a different meridional cross section by means of a tropic corresponding transformation of variables. A general solution of the problem of free torsional vibrations is obtained from which the
	Cord 1/2
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40282-65 CCESSION NR: AP5006171 colutions for particular cone are deduced. The residing ram show the effect restoropic cone for apexias: I figure and 25 for	of anisotropy on naturangles of 10, 20, and	cone and an isotropic ulations plotted in al frequencies of an 30°. Orig. art.	
SSOCIATION: none	ENCL: 00	SUB CODE: AS	
NO REF SOV: 002	OTHER: 001		
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81359

S/181/60/002/03/15/028 B006/B017

24.7700

AUTHORS: Bonch-Bruyevich, V. L., Gulyayev, Yu. Y.

N

TITLE:

On the Theory of Impact Recombination in Semiconductors

PERIODICAL:

Fizika tverdogo tela, 1960, Vol. 2, No. 3, pp. 465-473

TEXT: In the introduction, the authors briefly discuss some papers dealing with the influence exercised by the Auger effect on recombination processes in semiconductors. The present paper deals with the problem of impact recombination in semiconductors, taking into account the interaction between free carriers. Furthermore, the authors attempted to estimate the amount of the exchange term on the capture of minority carriers as well as the influence exercised by Coulomb forces on the capture of such carriers by charged centers. First, the impact recombination coefficients in neutral impurity centers are calculated by using the same approximation methods as in Refs. 4 - 6. According

to Ref. 8 $\Phi(\mathbf{r}) = \frac{Ze}{r} \exp(-q\mathbf{r})\cos q\mathbf{r}$ is chosen as interaction potential;

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On the Theory of Impact Recombination in Semiconductors

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 $\sqrt{\pi n} me^2 \sqrt{1/4}$, n is the concentration of free carriers. An n-type semiconductor is considered, i.e., recombination takes place at neutral centers. At a sufficiently high concentration of majority carriers, the recombination cross section is determined by the capture cross section of the minority carriers (holes). The processes contributing to the matrix element of the transition (from state n into state k) are schematically shown in Figs. 1 and 2. A general and some special expressions were obtained for the recombination coefficient. The capture cross section in n-type germanium at 300° K, β = m/m_o (ratio between effective and true carrier mass) - β = 0.2, trap depth $E_t \simeq 0.3$ ev (ΔE = 0.66 ev) is estimated to be $\sigma_p \simeq 10^{-34} n_o cm^2$; $\sigma_p \simeq 10^{-17} cm^2$ at n_o = 1017 cm⁻³. In the second chapter, the coefficient of impact recombination is again calculated by using another trap model ("trap radius" small compared with the thermal wavelength of the free carriers). In the third chapter, it is assumed that the recombination centers are charged, and the capture mechanism is investigated for this case. It was found that the charge sign of the trap exercises no influence on

Card 2/3

On the Theory of Impact Recombination in Semiconductors

81359 S/181/60/002/03/15/028 B006/B017

the impact-recombination mechanism. In a capture of carriers at charged centers, the recombination coefficient is reduced by the action of the Coulomb field (compared with neutral centers). This reduction is, however, within the error limits of the computations. There are 2 figures and 12 references: 6 Soviet, 3 US, 2 British, and 1 Polish.

ASSOCIATION: Institut radiotekhniki i elektroniki AN SSSR Moskva

(Institute of Radio Engineering and Electronics of the

AS USSR, Moscow)

SUBMITTED: May 23, 1959

V

Card 3/3

国际影响的

S/181/61/003/002/009/050 B102/B204

9.4300 (and 1035, 1143)

AUTHOR:

Gulyayev, Yu. V.

TITLE:

The statistics of the electron - hole recombination on

impurity centers in semiconductors

PERIODICAL: Fizika tverdogo tela, v. 3, no. 2, 1961, 382-383

TEXT: The carrier recombination on multiply charged centers in semiconductors has recently been repeatedly investigated, but the physical sense of the trapping coefficients introduced in the case, in which to a given charge state of the trap there correspond several excited states, was insufficiently well explained. In the present paper, the lifetime of the minority carriers in the latter case was calculated, and the sense of the corresponding trapping coefficients was explained. A non-degenerate semiconductor with sufficiently small trap concentration was investigated under steady conditions. The index n numbers the various excited states of the trap which capture j electrons. For the trapping rate $U_{nj}^{(n)}$ for electrons from the conduction band in the nj-th state of the trap and

S/181/61/003/002/009/050 B102/B204

The statistics of the electron - hole ...

the trapping rate $U_{nj}^{(p)}$ of the holes in the same state $U_{nj}^{(n)} = \sum_{m} C(m, j-1|n, j) \left\{ P_{m, j-1}^{n-P} n_{j}^{n} j_{mn} \right\}$ (1)

$$U_{n,j}^{(p)} = \sum_{m} D(n,j|m,j-1) \left\{ P_{n,j} P - P_{m,j-1} P_{j,nm} \right\}$$
 (2) is obtained. Here $C(...)$

and D(...) are the ordinary quantum-mechanic trapping coefficients for electrons and holes respectively in the nj-th state of the trap, multiplied by the trap concentration and averaged over the states of the carriers in the corresponding bands (if before electron- or after hole-trapping the trap is in the state (m,j-1)); n and p denote the total concentrations of the electrons and holes and P_n the non-equilibrium

probability for the nj-th state, and

$$n_{jmn} = N_c \frac{g_{m, j-1}}{g_{nj}} \exp\left\{\frac{E_n(j) - E_m(j-1) - E_c}{kT}\right\}, \tag{3}$$

$$p_{j_{nm}} = N_{o} \frac{g_{nj}}{g_{m,j-1}} \exp\left\{ \frac{E_{o} - E_{n}(j) + E_{m}(j-1)}{kT} \right\}$$
 (4)

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S/181/61/003/002/009/050 B102/B204

The statistics of the electron - hole ...

Here $\mathbf{E}_{\mathbf{n}}(\mathbf{j})$ and $\mathbf{g}_{\mathbf{nj}}$ are the energy and the multiplicity of the degeneration of the nj-th state in the trap, $\mathbf{N}_{\mathbf{c}}$ and $\mathbf{N}_{\mathbf{v}}$ the effective numbers of states in the bands. It is further assumed that the transition of the trap from one state to another without a change in the number of trapped electrons occurs within a considerably shorter time than a transition with change of the charge state of the trap. The Fermi quasilevel $\mu_{\mathbf{j}}$ may then be

introduced for the charge state of the trap, which permits simplifications. In the case of small deviations from equilibrium, the lifetime of the pairs thus results in P_{a}^{0}

$$\frac{1}{\tau} = (n_0 + p_0) \sum_{j=1}^{N} \sum_{n} \frac{P_{nj}^0}{D_{nj}^{-1} n_0 + P_{nj}^0 C_{nj}^{-1} p_0}.$$
 (5)

$$C_{nj} = \sum_{m} P_{m, j-1}^{0} C(m, j-1 | n, j),$$
 (6)

$$D_{nj} = \sum_{m} D(n, j | m, j-1), \tag{7}$$

where P_{nj}^{0} is the equilibrium probability of the nj-th state of the trap. Card 3/4

S/181/61/003/002/009/050 B102/B204

The statistics of the electron - hole ...

Here C. is the quantum-mechanical coefficient of electron capture onto the nj-th trap level averaged over the different excited states of the trap with (j-1) electrons, i.e. over the initial states of the trap. As Pm,j-1 depends exponentially on temperature, the coefficient C may also depend exponentially on temperature. Dn is the trapping coefficient of the holes onto the nj-th level of the trap, summated over the various states of the trap with (j-1) electrons, i.e. over the final states. Cn and Dn have a clear physical sense: they are averaged quantum-mechanical trapping coefficients. The author thanks S. G. Kalashnikov and V. L. Bonch-Bruyevich for discussion. There are 5 references: 1 Soviet-bloc and 4 non-Soviet-bloc.

ASSOCIATION: Institut radiotekhniki i elektroniki AN SSSR Moskva (Institute of Radioengineering and Electronics of the AS USSR, Moscow)

SUBMITTED: April 7, 1960

Card 4/4

GULYAYEV, Yu.V. Statistics of Fiz.tver.tela	electrons and ho 3 no.4:1094-11	les in semiconduc .00 Ap '61.	tors with disloca (MIRA l	tions. 4:4)
		ektroniki AN SSSR (Dislocations in	, Moskva. crystals)	

24.4400

S/181/62/004/005/031/055 B108/B112

AUTHOR:

Culyayev, Yu. V.

TITLE:

On the theory of carrier recombination on linear dislocations

in semiconductors

PERIODICAL: Fizika tverdogo tela, v. 4, no. 5, 1962, 1285 - 1289

TEXT: The effect of the Coulomb barrier at a dislocation on the electron capture upon a charged linear dislocation is calculated by a quantum mechanical method (V. L. Bonch-Bruyevich. FTT, sb. II, 182, 1959) in quasi-classical approximation. Owing to the tunnel effect, the Coulomb barrier is rather weak when the temperatures are not too low (** 100° K) barrier is rather weak when the temperatures are not too low (** 100° K) in the linear dislocation case, as well as in the case of impurity centers in the linear dislocation case, as well as in the case of impurity centers. At low temperatures the effect of the Coulomb barrier at the dislocation at low temperatures owing to deionization of the donor impurities and interease of the screening radius. When the temperature is lowered from crease of the screening radius. When the temperature is lowered from 100 to 12.5° K, the electron capture coefficient may decrease by some orders of magnitude. There is 1 table.

S/181/62/004/005/031/055 B108/B112

On the theory of carrier ...

ASSOCIATION: Institut radiotekhniki i elektroniki AN SSSR (Institute of

Radio Engineering and Electronics AS USSR) Moscow

January 2, 1962 SUBMITTED:

Card 2/2

CIA-RDP86-00513R000617320017-4 "APPROVED FOR RELEASE: 09/19/2001

L 18393-63 EWT(1)/EWG(k)/EDS/ES(w)-2AFFTC/ASD/ESD-3/IJP(C)/SSD/AFWL

Pi-4/Po-4/Pab-4/Pz-4

ACCESSION NR: AP3003718

\$/0109/63/008/007/1179/1186

AUTHOR: Bonch-Bruyevich, V. L.; Gulyayev, Yu. V.

TITLE:

Mechanism of generating plasma oscillations in a semiconductor

SOURCE: Radiotekhnika i elektronika, v. 8, no. 7, 1963, 1179-1186

TOPIC TAGS: plasma oscillation, semiconductor

ABSTRACT: Transformation of energy supplied to a semiconductor into plasmaoscillation energy was investigated by D. Pines and J. R. Schrieffer (Phys. Rev., 1961, 124, 5, 1387). The present article deals with the subject on a wider scale; it considers theoretically all possible types of oscillations with an allowance for recombination of carriers. Bipolar-plasma waves in an isotropic homeopolar semiconductor are generated by a stream of electrons. The hydrodynamic approximation is used in setting up the initial differential equations describing concentrations and average velocities. Both types of plasma oscillations,

Card 1/2

CIA-RDP86-00513R000617320017-4" **APPROVED FOR RELEASE: 09/19/2001**

L 18393-63

ACCESSION NR: AP3003718

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"optical" and "acoustical," are dealt with. Conditions of excitation of oscillations are examined, and the critical drift velocity ($10^6 - 10^6$ cm/sec) is found. Effective mass of donors is determined. It is inferred that: (1) generation of low-frequency plasma oscillations is easily realizable; (2) the possibility of generating high-frequency oscillations is not clear. "The work was resumed on the initiative of S. G. Kalashnikov to whom the authors are greatly indebted for his support and discussing the results and the possibility of experimental verification. The authors are thankful to M. Ye. Gertsenshteyn and V. I. Pustovoyt for their permission to read their work before its publication." Orig. art. has: 33 formulas.

ASSOCIATION: none

SUBMITTED: 26Jun62

DATE ACQ: 02Aug63

FINCL: 00

SUB CODE: GE

NO REF SOV: 006

OTHER: 003

Card 2/2

L 22186-65 EWA(h)/EWG(k)/EWT(1)/T/ Peb/Pr-6ASDA-5/AFWL/ESD/HSD/AFWDT/ESDC/ESTG(s)
LJP(c) AT

ACCESSION NR: AP5001848

S/0056/64/047/006/2251/2253

AUTHOR: Gulyayev, Yu. V.; Pustovoyt, V. I.

TITLE: Amplification of surface waves in semiconductors

SOURCE: Zhurnel eksperimental'noy i teoreticheskoy fiziki, v. 47, no. 6, 1964, 2251-2253

TOPIC TAGS: surface wave, wave amplification, semiconductor, carrier density, carrier mobility, sound speed, piezoelectricity

ABSTRACT: It is shown by a quasihydrodynamic analysis that surface waves can be amplified in a layered system consisting of a thin semiconducting layer and a semi-infinite piezoelectric (or vice versa), using the phenomenon whereby the electric field that accompanies an elastic wave in the piezoelectric penetrates into the semiconductor, in which the carriers move in a definite direction. This is analogous to the amplification of acoustic waves observed in semiconductors when the carrier drift velocity exceeds the phase velocity of the acoustic wave. In the case considered here amplification will take place when the directional velocity of the carriers in the superconductor exceeds the phase velocity of the

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ACCESSION NR: AP5001848

surface waves. If amplification is effected, the power per unit volume of the semiconductor can be markedly reduced by using a semiconductor with large carrier mobility. For example, for pure InSb with approximate carrier density 10^{12} cm⁻³ and mobility 10^{14} cm²/V·sec the power dissipation is about 0.1 W/cm³, which is much lower than in the case of CdS. It is pointed out in the conclusion that a similar analysis can be applied to other types of surface waves, particularly plasma waves. "We thank V. L. Ginzburg, S. G. Kalashnikov, V. L. Bonch-Bruyevich, and L. V. Keldy*sh for a discussion of the work." Orig. art. has: 4 figures.

ASSOCIATION: Institut radiotekhniki i elektroniki Akademii mauk ESSR (Institute of Radio Engineering and Electronics, Academy of Sciences SSSR); Institut fizikotekhnicheskikh i radiotekhnicheskikh izmereniy (Institute of Physicotechnical and Radio Measurements).

SUBMITTED: 20Jun64

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	ACCESSION NR: AP5014233 UR/0386/65/001/003/0011/0015
	AUTHOR: Gulyayev, Yu. V. TITLE: The Faraday effect on "hot" electrons in semiconducture. SOURCE: Zhurnal eksperimental noy i teoreticheskoy fiziki. Pis'na v redaktsiyu.
	Title: The raraday effect on mot effections in semicomputations.
	SOURCE: Zhurnal eksperimental'noy i teoreticheskoy fiziki. Pis'na v redaktsiyu. Prilozheniye, v. 1, no. 3, 1965, 11-15
	TOPIC TAGS: semiconductor theory, electron gas, Faraday effect, electric polariza- tion
	ABSTRACT: The various characteristics of a semiconductor (electrical conductivity, magnetoresistance, thermomagnetic effect, etc.) may be considerably altered by heating the electron gas in the semiconductor. The author examines the effect:
	which heating of the electron gas has on Faraday rotation of the plane of polariza- tion of an electromagnetic wave passing through the semiconductor. The degree of "hotness" of the electron gas is given by the electron temperature "which differs
	from the lattice temperature T_0 . It is assumed that the magnetic field is weak, and that the frequency of the electromagnetic wave is rather low, so that quantum ef-
	fects may be disregarded. A unipolar semiconductor is considered in which the cur-
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L 1424-66 EMT(1) / IJP(c) ACCESSION NR: AP5021138

UR/0386/65/002/001/0003/0006

AUTHOR: Gulyayev. Yu. V.

TITLE: Possible existence of "second" spin waves in ferromagnets

SOURCE: Zhurnal eksperimental'noy i teoreticheskoy fiziki. Pis'ma v redaktsiyu.

Prilozheniye, v. 2, no. 1, 1965, 3-6

TOPIC TAGS: spin wave theory, sound wave, spin phonon interaction, ferromagnetism collision integral

ABSTRACT: The author examines the possible existence of secondary excitations in the system of magnons in a ferromagnet. In analogy with second sound, these secondary excitations are called "second spin waves" to distinguish them from the "first" waves, the magnons themselves. Neglecting magnetic dipole-dipole interaction between the spins of the atom and the spin-orbit interaction, it is shown that in some temperature range above the Curie point the magnon gas in the ferromagnet is perfectly analogous to a gas of molecules that collide relatively frequently with one another and rarely experience inelastic collisions accompanied by a change in the number of particles. Just as second sound waves can propagate in such a gas, second spin waves can propagate in the magnon. The velocity of the spin waves at room temperature is estimated to be of the order of 100 cm/sec for

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L 1424-66

ACCESSION NR: AP5021138

15

most ferromagnets. Relaxation times of the order of 10-13 and 10-6 are estimated for intermagnon collisions in which the number of magnons is conserved, and for scattering involving a change in the number of magnons (in the total magnetic moment of the system), respectively. It is also shown that the dispersion of the second spin waves is linear, and that these waves should manifest themselves as macroscopic waves of the magnetization, of the spin specific heat (or the spin temperature), and of similar thermodynamic quantities. Measurement of the velocity of second spin waves could yield independent information on the magnitude of the exchange integral I. In addition, one can apparently expect a unique resonant interaction in a crystal between second spin waves and ordinary sound waves that also possess a linear dispersion law and a nearly equal propagation velocity. "The author is grateful to V. L. Bonch-Bruyevich, S. G. Kalashnikov, A. V. Vashkovskiy, and Ya. A. Monosov for a discussion of the work." Orig. art. has: 6 formulas.

ASSOCIATION: Institut radiotekhniki i elektroniki Akademii nauk SSSR (Institute of Radio Engineering and Electronics, Adademy of Sciences, SSSR)

8UBMITTED: 14May65 ENCL: 00

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NO REF SOV: 00

OTHER: 001

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j. 9253-66 EWT(1)/EWA(m)-2 IJP(c) AT

ACC NR: AP5022722 SOURCE CODE: UR/0181/65/007/009/2772/2779/

AUTHOR: Gulyayev, Yu. V.; Zil'berman, P. Ye.

ORG: Institute of Radio Engineering and Electronics, Moscow (Institut radiotekhniki i elektroniki)

TITLE: Resonance amplification of Rayleigh ultrasonic waves by a beam of charged particles passing close to the surface of a crystal

SOURCE: Fizika tverdogo tela, v. 7, no. 9, 1965, 2772-2779

TOPIC TAGS: semiconductor theory, Rayleigh wave, ultrasonic amplification, cadmium sulfide, plasma charged particle, plasma resonance, electron beam

ABSTRACT: The authors study the interaction between surface (Rayleigh) waves in a CdS type crystal and a beam of electrons passing through fissures of arbitrary width inside the crystal. When a fissure is wide, the curve for amplification as a function of frequency is a set of non-overlapping spikes. Under optimum conditions, the amplification may be as high as 0400 db/cm. However, in practical instances it is of the order of 1 db/cm at 01 Mc. It is shown that convective instability may appear at resonance (coincidence of frequencies and phase velocities) of the Rayleigh and plasma waves in the beam. Dispersion curves are plotted for studying the nature of this instability. It is found that the maximum amplification is reached at the lowest re-

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ACC NR: AP6016836 (N) SOURCE CODE: UR/0046/66/012/002/0253/0255

AUTHOR: Gulyayev, Yu. V.

ORG: Institute of Radio Engineering and Electronics, AN SSSR (Institut radiotekhni-

ki i elektroniki AN SSSR)

TITLE: Rotation of the plane of polarization of sound in a magnetic field in piezo-electric semiconductors

SOURCE: Akusticheskiy zhurnal, v. 12, no. 2, 1966, 253-255

TOPIC TAGS: piezoelectric crystal, cadmium sulfide, ultrasonic wave propagation, dispersion equation, dielectric constant, semiconductor carrier, carrier scattering, Sound wave, Electro masseric wive ABSTRACT: The semiconductor considered is CdS oriented in such a way that its

ABSTRACT: The semiconductor considered is CdS oriented in such a way that its crystallograpic axes coincide with the coordinate axes. A plane-polarized transverse ultrasonic wave propagates along the Z axis, and constant magnetic and electric fields Ho and Fo are applied along the same axis. A dispersion equation is obtained for the coupled electromagnetic and sound waves in terms of the left- and right-hand polarization components of the plane-polarized wave and the complex dielectric constant for these waves. The strong interaction between the electromagnetic and the sound waves occurs when the separate dispersion curves for the sound

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wave and for the electromagnetic waves intersect. In view of the weak coupling between the sound and helicon waves, a resonant interaction between them is possible only in a sufficiently large constant electric field. An expression is obtained for the rotation of the plane of polarization of the sound wave under such conditions. It is concluded that observation of this rotation by experiment would yield information on the piezoelectric constants, on the carrier scattering mechanism, and other data. The author thanks S. G. Kalashnikov and V. L. Bonch-Bruyevich for a discussion of the work. Orig. art. has: 4 formulas.

SUB CODE: 20/ SUBM DATE: 05Apr65/ ORIG REF: 003

Card 2/2/114P

ACC NR. AP6036986 (A, N) SOURCE CODE: UR/0181/66/008/011/3366/3372

AUTHOR: Gulyayev, Yu. V.

ORG: Institute of Radio Engineering and Electronics AN SSSR, Moscow (Institut radio-tekhniki i elektroniki AN SSSR)

TITLE: Contribution to the theory of transport phenomena connected with the dragging of electrons by ultrasonic waves in solids.

SOURCE: Fizika tverdogo tela, v. 8, no. 11, 1966, 3366-3372

TOPIC TAGS: transport phenomenon, kinetic theory, electron interaction, phonon drag, electron gas, ultrasonic effect, electron mobility, acoustic propagation

ABSTRACT: The author develops the kinetic theory of certain transport phenomena connected with the transfer of momentum from sound waves to conduction electrons and the resultant dragging of the latter in the direction of the sound. The analysis is confined to wavelengths which are much longer than the electron mean free path. The sound waves are excited in a crystal situated in an external magnetic field perpendicular to the direction of the sound flux. The sound intensity is assumed weak and heating of the electron gas by the wave is neglected. In view of the fact that the ultrasound wave exerts a different dragging force on electrons with different energies, this leads to violation of the relations derived for this effect by G. Weinreich (Phys. Rev. v. 107, 327, 1957), since the latter were based on collective action of the electrons, whereas actually at each instant of time there exist in the crystal

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ACC NR: AP6036986

spatially separated groups of electrons of different energy, characterized in general by different relaxation times, and consequently by different mobilities. The possibility that a propagating sound wave in a degenerate conductor can give rise to a longitudinal temperature gradient is predicted. It is shown that in the case of a degenerate electron gas, the acousto-electric effects of Ettingshausen and Peltier (and similar effects which are connected in principle with the energy scatter of the electrons) differs from the magnitude of the effects predicted in this paper by the square of the ratio of the Fermi energy to the thermal energy. The author thanks V. L. Bonch-Bruyevich, L. V. Keldysh, A. I. Morozov, and E. M. Epshteyn for a discussion of the work. Orig. art. has: 16 formulas.

SUB CODE: 20/ SUBM DATE: 28Max66/ ORIG REF: 004/ OTH REF: 005

Card 2/2

SHEREDEKO, V.M., inzh.; GULYAYEVA, A.G., inzh.

Two-stage filtration of fats without intermediate receiver.
Masl.-zhir. prom. 24 no.10:38-39 58. (MIRA 11:10)

1. Kuybyshevskiy zhirovoy kombinat. (Kuybyshev--Filters and filtration) (Kuybyshev--Oil and fats)

APPROVED FOR RELEASE: 09/19/2001 CIA-RDP86-00513R000617320017-4"

CONTAINA, A. 1.
"Treatment of Superior Prognathism," Stomatologiya, No. 3, 1948. Chair Orthopedic Stomatol. Moscow Stomatological Inst.

ALEKSANDROV, B.M., nauchnyy sotrudnik; ALEKSANDROVA, T.N., nauchnyy sotrudnik; BELYAYEVA, K.I., nauchnyy sotrudnik; GORDUNOVA, Z.A., nauchnyy sotrudnik; GORDEYEVA, L.N., nauchnyy sotrudnik; GULYAYEVA, A.M., nauchnyy sotrudnik; DMITRENKO, Yu.S., nauchnyy sotrudnik; ZABOLOTSKIY, A.A., nauchnyy sotrudnik; MAKAROVA, Ye.F., nauchnyy sotrudnik; NOVIKOV, P.I., nauchnyy sotrudnik; POKROVSKIY, V.V., nauchnyy sotrudnik; SMIRNOV, A.F., nauchnyy sotrudnik; STEFANOVSKAYA, A.F., nauchnyy sotrudnik; BALAGUROVA, M.V., nauchnyy sotrudnik; VEBER, D.G., nauchnyy sotrudnik; POTAPOVA, O.I., nauchnyy sotrudnik; SOKOLOVA, V.A., nauchnyy sotrudnik; FILIMONOVA, Z.I., nauchnyy sotrudnik; POPENKO, L.K., nauchnyy sotrudnik; ZYTSAR¹, N.A., red.; PRAVDIN, I.F., red.; PANKRASHOV, A.P., red.; SHEVCHENKO, L.V., tekhn.red.

[Lakes of Karelia; natural features, fishes, and fisheries] Omera Karelii; priroda, ryby i rybnoe khoziaistvo; spravochnik. Petrozavodsk, Gos.izd-vo Karel'skoi ASSR, 1959. 618 p. (MIRA 13:8) (Continued on next card)

ALEKSANDROV, B.M. --- (continued) Card 2.

1. Russia (1917- R.S.F.S.R.) Karel'skiy ekonomicheskiy administrativnyy rayon. Sovet narodnogo khozyaystva. 2. Karel'skoye otdeleniye Vsesoyuznogo nauchno-issledovatel'skogo instituta ozernogo i rechnogo rybnogo khozyaystva (for Aleksandrov, Aleksandrova, Belyayeva, Gorbunova, Gordeyeva-Pertseva, Gordeyeva, Gulyayeva, Dmitrenko, Zabolotskiy, Makarova, Novikov, Pokrovskiy, Smirnov, Stefanovskaya, Urban). 3. Karel'skiy filial AN SSSR (for Balagurova, Veber, Potapova, Sokolova, Filimonova, Popenko).

(Karelia--Lakes)

APPROVED FOR RELEASE: 09/19/2001 CIA-RDP86-00513R000617320017-4"

GULYAYEVA, A.M.; DMITRIYENKO, Yu.S.; KUDERSKIY, L.A.

Results of the introduction of the Baikal whitefish in Lake Ukshozero (southern Karelia), Zool. zhur. 42 no.6: 877-881 '69. (MIRA 16:7)

1. Karelian Department of the State Research Institute of the Lake and River Fishery Management, Petrozavodsk.

(Ukshozero, Lake---Whitefishes)

(Fish introduction)

KORNEYEV, A.M., doktor ekor. mank; VIIIII.hil, 1.44., 1981-1981.

nauk; SHOKIN, H.A., kand. ekon. mank; 11VM 11.0, 1981.

doktor ekon. nauk; KOZIAV, Tu.K., kand. ekon. nauk;
VARANKIN, V.V., kand. ekon. nauk; hOZMARELID, Sh.L., doktor
ekon. nauk; OLATSKIY, L.V., doktor ekon. timak; hAROVETERAYA,
V.S., red.; GULTAYEVA, A.U., red.

[Industry in the administrative complex of the economic regions of the U.S.S.R.] Fromyshlemost' v knovimistvennos komplekse ekonomicheskikh saiorev SESR. Meskva, Maska, Maska, 566 p. (SRA 19:1)

1. Akademiya nauk SSSA. Institut ekonomiki.

L 06431-67 EWT(m)/EWP(t)/ETI IJP(c)JD/JG ACC NRI AP6026708 SOURCE CODE: UR/0181/66/008/008/2472/2473 AUTHOR: Gulyayeva, A. S.; Ivleva, V. S.; Iglitsyn, M. I. ORG: State Scientific Research and Design Institute of the Bare Metal Industry, Moscow (Gosudarstvennyy nauchno-issledovatel skiy i proyektnyy institut redkometallicheskoy promyshlennosti) TITLE: Lifetime of excess charge carriers in InSb single crystals with Ge and Au impurities SOURCE: Fizika tverdogo tela, v. 8, no. 8, 1966, 2472-2473 TOPIC TAGS: indium compound, antimonide, carrier lifetime, recombination ABSTRACT: The object of the work was to determine the effect of doping InSb single crystals with Go and Au impurities on the recombination of excess carriors. p-Type samples were obtained from the original n-type material (electron concentration 10^{14} cm⁻³) by this doping. The carrier lifetimes τ_n were measured at 77-300 K by stationary methods of measurement of the photomagnetic effect $(\tau_{\rm pn})$ and photoconductivity $(\tau_{\rm pc})$. The lifetime of electrons is inversely proportional to the concentration of traps. At 77°K, in samples doped with Ge, the quantity $\tau_{\rm n} = \tau_{\rm pm}$ changes by less than an order of magnitude as the Ge concentration increases by a factor of 200. This indicates that the recombination does not take place on Go atoms. The lifetime data show that the Ge impurity does not affect the recombination of excess carriers. In the 77-170 %

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s conclud ess carri	the lifetimes in samples doped with Ge and Au are approximately the same. It cluded that in this range, Ge and Au have no effect on the recombination of exactuded that in this range, Ge and Au have no effect on the recombination of exactuded that in this range, Ge and Au have no effect on the recombination of exactuded that in this range, Ge and Au have no effect on the recombination of exactuded that in this range, Ge and Au have no effect on the recombination of exactuded that in this range, Ge and Au have no effect on the recombination of exactuded that in this range, Ge and Au have no effect on the recombination of exactuded that in this range, Ge and Au have no effect on the recombination of exactuded that in this range, Ge and Au have no effect on the recombination of exactuded that in this range, Ge and Au have no effect on the recombination of exactuded that in this range, Ge and Au have no effect on the recombination of exactuded that in this range, Ge and Au have no effect on the recombination of exactuded that in this range, Ge and Au have no effect on the recombination of exactuded that it is a supplication of the recombination of exactuded that it is a supplication of the recombination of exactuded that it is a supplication of the recombination of exactuded that it is a supplication of the recombination of exactuded that it is a supplication of exactuded that it is a supplication of exactuded the recombination of exactuded that it is a supplication of exactuded the recombination of									
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ACCESSION NR: AP4034947

5/0181/64/006/005/1552/1554

AUTHORS: Gulyayeva, A. S.; Iglitsy*n, M. I.; Petrova, L. V.

TITLE: The lifetime of charge carriers in disequilibrium in single crystals of indium antimonide

SOURCE: Fizika tverdogo tela, v. 6, no. 5, 1964, 1552-1554

TOPIC TAGS: charge lifetime, temperature dependence, photogalvanometric determination, photoconductive determination, charge carrier adhesion, Auger recombination

ABSTRACT: The temperature dependence of the lifetime of nonequilibrium charge , carriers in InSb was investigated. Naturally alloyed (zone-melting) single crystals of both p and n types having a basic carrier concentration of 7 x 10¹³ - 4.5 x 10¹⁴ per cm³ were studied in the 78-300K temperature range. Measurements were made by photogalvenometric (FM) and photoconductive (FC) methods. A 500-watt tungsten light source was modulated at 1100 cps. The magnetic field was 0.205 webers/m². The samples were 14 x 4 x 1.5 mm³ parallelograms polished and cleansed with CP-4A. Comparison was made with theoretical relationships presented by S. Kurnick and R. Zitter (J. Appl. Phys., 27, 278, 1956) and by R. Zitter, A. Strauss, and A. Attard (Phys. Rev., 115, 226, 1959). Typical results are shown in Figures 1 and 2 on the

ACCESSION NR: AP4034947

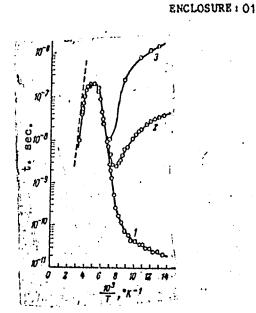
Enclosures. The character of the curves was the same for both measurement methods. For all samples (except a few n-type ones near the liquid nitrogen temperature) results differed ($\tau_{FC} > \tau_{FM}$) due to the adhesion of secondary carriers. At higher temperatures the difference disappeared, and the lifetime reached a maximum τ_{max} of 4×10^{-7} , $\times 10^{-7}$ sec between 170 and 200K. The results, when analyzed together with the eneral theory of recombination and the previous experimental data, showed that it was necessary to consider two separate temperature ranges. Below 250K, recombinations of local centers predominated. The defining parameters were charge concentration, energy state, and degeneracy multiple. In this study samples contained uninvestigated residual contaminants, so that the parameters remained unknown. By assuming that recombinations occurred at the centers with the same parameters as those given by R. Laff and H. Fam (Phys. Rev., 121, 53, 1961), calculations were made to give electron τ_n and hole τ_p lifetimes. Experimental values and theoretical calculations differed by a value greater than could be explained by normal error. At temperatures above 250K Auger recombinations are most important. Orig. art. has: 2 figures.

ASSOCIATION: Gosudarstvenny*y nauchno-issledovatel'skiy i proyektny*y institut redkometallicheskoy promy*shlennosti, Moscow (State Scientific Research and Design Card 2/5

CCESSION NR: AP4034947 Institute of the Rare Metal Industry)							
UBMITTED: 21Dec63 DATE ACQ: 2CMay64 ENCL: 0							
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ACCESSION NR: AP4034947

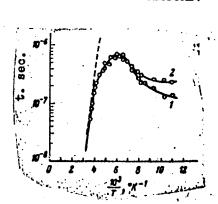
Fig. 1. Temperature characteristics of lifetime in p-type InSb.
(1) \mathcal{T}_{FM} and \mathcal{T}_{n} ; (2) \mathcal{T}_{FC} ; (3) \mathcal{T}_{p} .



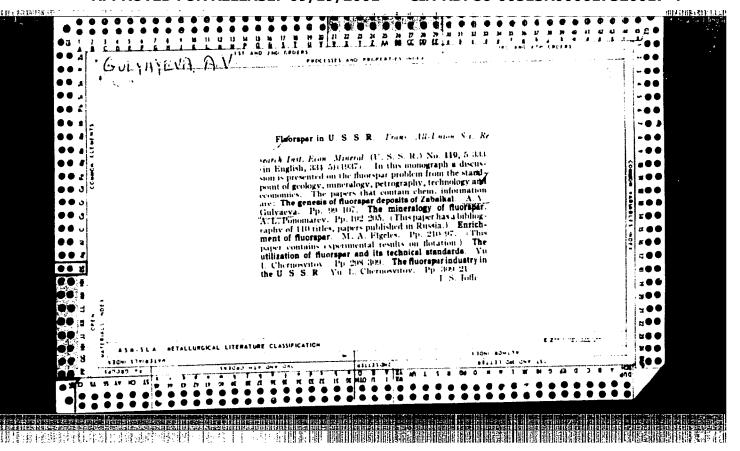
ACCESSION NR: AP4034947

ENCLOSURE: 02

Fig. 2. Temperature characteristics of lifetime in n-type InSb.
(1) \mathcal{T}_{FM} ; (2) \mathcal{T}_{FC} .



Card 5/5



GULYAYEVA, A. V.

Gulyayeva, A. V. - "On certain prospectin indications of flourspar", Trudy Vsesoyuz. nauch.-issled. in-ta mineral. syr'ya, Novaya seriya, Issue 1, 1949, p. 3-6, - Bibliog: 7 items.

SO: U-4631, 16 Sept. 1953, (Letopis 'nykh Statey, No. 24, 1949).

USSR / Cultivated Plants. Cereal Crops.

M-3

Abs Jour

: Ref Zhur - Biologiya, No 13, 1958, No. 58548

Author

: Gulyayova, E.

Inst

: Not given

Title

The Importance of Alien Pollen in Growing Self-Pollinating

Strains of Corn

Orig Pub

: Zemledeliye i zhivetnovodstvo Moldavii, 1957, No 5, 41-46

Abstract

* The pollens of sorghum, African millet, winter rye, wheat, sunflower, squash, hibiscus and orache were used as alien pollens in the self pollination of local Moldavian varieties and Dnepropetrovsk variety in experiments which took place during 1953-1956. The experiments were conducted under conditions of strict isolation. 3-4 days old corn stigmas were subjected to pollination. The foreign pollen increased the percentage of germinated grains in the cob in all variances, particularly in dry

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Cereal Crops.

M-3

Abs Jour : Ref Zhur - Biologiya, No 13, 1958, No. 58548

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by foreign pollen, were found in the cobs. Sprouts caused by pollination by pollens of sunflower and winter rye developed much faster than the control barch. Sprouts resulting from pollination by the pollen of serghum, African millet and squash were depressed. Differences were noticed in the amounts of leaves and cobs, the shape of the staminate flowers, the coloration of the grains and so on. The yield increased in comparison with self-pollinating strains by 1.8-2.3 times, depending on variances, and was 60-83% of the initial variety. The strains resulting from pollination with hibicus and orache pollen were characterized by their vegetative mass. --

Card 2/2

GULYAYEVA, E.G.: KALANTAROV, K.D.

KRASIOV, M.L., prof.; GRISHINA, V.I.; SIVOSHIPSKIY. D.S.; MILOVIDOVA, I.A.; AGRAMAY, V.Z.; GULYAYEVA, E.G.; KOLONTAROV, K.D.

Clinical method of diganosing intraocular temors using radicactive phosphorus. Vest.oft. no.3:3-9 Ny-Je 162. (MIRA 15:8)

1. Kafedra glaznykh bolezney i kafedra meditsinskoy radiologii TSentval'nogo instituta usovershenstvovaniya vrachey (for Krasnov, Grishina, Sivoshinskiy). 2. Moskovskaya glaznaya klinicheskaya bol'nitsa (for Milovidova). 3. Vsesoyuznyy nauchno-issledovatel'skiy instituta meditsinskogo instrumentariya i oborudovaniya (for Agranat, Gulyayeva, Kolontarov).

(EYE--TUMORS) (PHOSPHORUS--ISOTOPES)

GULYAYEVA, F.Ye.

Changes in the rate of blood flow under the influence of neurotropic substances. Terap. arkh. 28 no.4:41-44 *56. (MIRA 9:9)

1. Iz gospital noy terapevticheskoy kliniki (dir.-deystvitel nyy chlen AMN SSSR prof. A.L. Myasnikov) I Moskovskogo ordena Lenina meditsinskogo instituta imeni I.M.Sechenova.

(BLOOD CIRCULATION

flow rate, eff. of CNS funct., determ. with aminoacetophenetidin & amobarbital sodium)

(CENTRAL NERVOUS SYSTEM, physiol.

eff. on blood flow rate, determ. with aminoacetophenetidin & amobarbital sodium)

(ACETOPHENETIDIN, deriv.

aminoacetophenetidin, eff. on CNS in determ. of CNS regulation of blood flow)

(BARBITURATES, eff.

amobarbital acdium, on CNS in determ of CNS regulation of blood flow)

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AUTHORS:

Dunayev, F.N., and Gulyayeva, G.P.

TITLE:

The influence of elastic compression on the initial reversible magnetic susceptibility of ferro-magnetics

PERIODICAL: Izvestiya vysshikh uchebnykh zavedeniy, Fizika,

no.5, 1961, 44-48

TEXT: On the basis of Ye.I. Kondorskiy's theory, S.V. Vonsovskiy (Ref. 2: ZhETF, Vol. 17, 1094, 1947) developed a theory of initial reversible magnetic susceptibility which took account of weak magnetic fields as well as of elastic stresses, which also displace the domain boundaries. The theory has been checked in tests made with tensile stresses but hitherto compressive loads have not been tried, and this is the object of the present article. The experimental materials were chosen to cover a range of constants of magnetic anisotropy and of magnetostriction. The samples were mechanically worked and heat treated in various ways. The initial tests were made on workhardened samples with high internal stresses. The work hardening was set up by rolling or forging. Then all samples were given Card 1/7/<

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No.1 annealing for 6 hours at 600 °C in a vacuum of 10-4 mm Hg and reinvestigated. All the samples were then given No. 2 annealing, two hours at 900 °C in vacuum, and retested. Samples of 66-permalloy were also given annealing No.3 at 550 °C for 20 min, cooling at a rate of 100 °C/hour in a longitudinal magnetic field of 25 oersted, to set up a magnetic texture. Table 1 gives the composition of the materials investigated, the sample sizes and The magnetic permeability coercive force in various conditions. was measured by the ballistic method and the initial permeability was determined by extrapolating the permeability measured in weak fields to zero field. The maximum error of determination of A special rig was devised to apply permeability was about 6%. compressive stresses to the samples, most of the samples being covered with tubular guides to avoid bending. The error in determination of the stress was about 1%. The coercive force was determined to give a qualitative assessment of the influence of internal stresses after the various heat treatments. Curves of magnetic induction and magnetostriction were determined to find the character of the magnetic texture. The magnetostriction

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curves were determined by means of wire strain gauges. shows curves of the initial permeability of transformer steel with 4.1% Si as function of the compressive loading in kg/mm². relates to the work hardened specimen, curve 2 after No.1 annealing, and curve 3 after No.2 annealing. It will be seen that the two annealings considerably relieve the internal stresses and increase the initial permeability. Similar curves were obtained for transformer steel containing 3.4% Si, for the dynamo steels and for the armco iron. Similar relationships are also obtained for the 66-permalloy which was not subject to thermal magnetic treatment except that the initial susceptibility of the workhardened specimen was practically independent of the load. initial part of the curve for armco iron there is a clearly expressed maximum. These results are explained in terms of Vonsovskiy's theory: they correspond to the results that would be expected for materials with a positive magneto-striction constant λ_{100} and an axis of easy magnetisation of the type [100].



Fig. 4 shows the relationship between the initial permeability of electrolytic nickel and the compressive load. Curve 1 is for the Card 3/7

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work hardened condition, curve 2 after No.1 annealing, and curve 3 after No.2 annealing: again the load is given in kg/mm². Nickel has negative magnetostriction and an axis of easy magnetisation of the type [111] and for this case Vonsovskiy's theory indicates the presence of a maximum in the curve of the initial permeability of the nickel as function of the compressive load, as is indeed observed. Curve 4 on Fig.4 was obtained on a specimen which had received No.2 annealing and was then slightly work hardened by bending, and it will be seen that this reduces the value of the initial permeability and displaces the maximum relative to curve 3 towards higher loads, as is predicted by Vonsovskiy's theory. It is concluded that the experimental data are in good qualitative agreement with Vonsovskiy's theory. Ya.S. Shur and D.D. Mishin are mentioned in the article for their contributions in this field.

There are 4 figures, 1 table and 9 references: 8 Soviet-bloc and the following English language reference:

Ref. 5: E. Williams, Phys. Rev., Vol. 52, 747, 1004, 1937.

Card 4/7/5

The influence of elastic compression... \$/139/61/000/005/005/014 E194/E135

ASSOCIATION: Ural'skiy gosuniversitet imeni A.M. Gor'kogo (Ural State University imeni A.M. Gor'kiy)

SUBMITTED: July 19, 1960

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AUTHORS:

Korzh, P. D., Gulyayeva, G. P.

HILE

The thermoelectric method of determining St in Pb-Sb alloys

FERIOTICAL

Referativnyy zhurnal, Metallurgiya, no. 2, 1962, 14, abstract 2K69

("Sb. nauchn. tr. Magnitogorskiy gornometallurg. in-t", no. 23,

1961, 12-19)

The thermoelectric method of determining Sb in Pb-Sb alloys is described. The method is based on measuring the relation between the thermoelectromotive force and Sb concentration. Three methods of contacting samples with a comparison element were tried. 1) Sn soldering, 2) a contact by means of mechanical clamps, 3) a contact through a molten metal. By the third method the alloy sample and the comparison element were submerged, with one end, into a molten Wood's alloy. The thermoelectromotive force of Pb-Sb samples was measured on the NNTB -1 (PPTV-1) direct current potentiometer by the compensation method. Bi was used as comparison element. The Sb content was studied in binary alloys containing 4.7 - 8.5% Sb. The calibration curve is plotted as follows ene junction formed by the sample and Bi electrode was heated in

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coiling water, other ends being at 18° C. The thermoelectromotive force was measured 10 - 15 times. It was found that the thermoelectromotive force of Pt-St arleys decreases with an increased Sb content by the linear law. The deviation of individual determinations from the mean value did not exceed + 0.18%. There are 6 references.

V. Pedanova

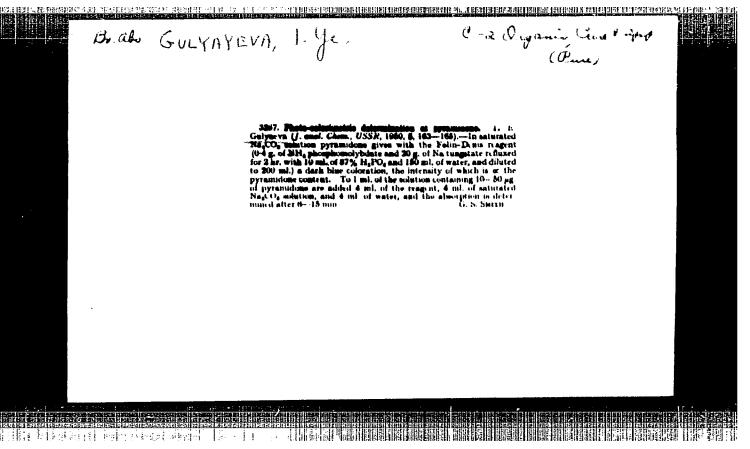
[Abstracter's note. Complete translation]

Card 2/2

KORZH, P.D.; GULYAYEVA, G.P.; GINIYATULIN, I.N.

Thermcelectric method for determining antimony in lead-antimony alloys. Zav.lab. 29 no.3:289-291 '63. (MIRA 16:2)

1. Magnitogorskiy gorno-metallurgicheskiy institut.
(Antimony--Analysis) (Lea-antimony alloys)
(Thermoelectricity)



TELYAYOVA, 1. P., Jane Med Sci -- (disr) "Ploop mirrile to effice attending region,"

Khar'kov, 1990, 8 pp (Khar'kov Sta a Lealcal Institute) (Et. 19-00, 140)

L 28537-66 EWP(j)/EWT(m)/T/EWP(t)/ETI IJP(c) RM/WN/JD/WB/GD

ACC NR: AT6013804

SOURCE CODE: UR/0000/65/000/000/0296/0304

AUTHOR: Rozenfel'd, I. L.; Persiantseva, V. P.; Gulyayeva, I. P.

57

ORG: none

TITLE: Protective properties of inorganic inhibitors in the presence of extraneous ions

SOURCE: Korroziya metallov i splavov (Corrosion of metals and alloys), no. 2. Moscow, Izd-vo Metallurgiya, 1965, 296-304

TOPIC TAGS: corrosion inhibitor, ion, sodium compound, sulfate, chloride, electrolyte

ABSTRACT: Inorganic inhibitors, which chiefly include sodium and potassium salts of acids whose anions contain atoms of elements V,/IV and VII of the periodic table, are widely used to protect metals against corrosion in neutral media. Yet despite the numerous studies of these inhibitors, the interaction between inhibiting and aggressive media still has not been adequately investigated and hence the effectiveness of the inhibitors in various electrolytes cannot be predicted. To fill this gap, the authors investigated the corrosion rate of Fe as a function of inhibitor concentration for a fixed concentration of aggressive ions (Cl⁻, SO²₄). In addition the protective concentrations of inhibitors for various concentrations of aggressive ions were investigated; this made it possible to derive a mathematical relation for

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calculating the required amount of inhibitor for real systems. Thus the dependence of the protective concentration of such compounds as Na₂WO₄, Na₃PO₄, Na₂MoO₄, NaH₂PO₄ on the content of sulfate ions (SO₄-) in the solution is expressed by the equation: Y = 0.17X + 0.003, where Y is molal inhibitor concentration, and X is molal concentration of aggressive ion. For the aggressive ion Cl⁴ the corresponding relation is: Y = 0.38X + 0.005. The accompanying electrochemical tests pertained to electrode impedance which, as was anticipated, differed depending on whether the inhibitor forms phase layers or adsorption layers at the surface of the protected metal. The corrosion rate of metal as a function of inhibitor concentration in a solution of 30 mg/liter NaCl and 70 mg/liter Na₂SO₄ was found to decrease in all cases -- except monosubstituted phosphate and sodium vanadate -- with increasing inhibitor concentration (Fig. 1). Thus, the investigated inhibitors may be arranged in the following series of increasing protective capacity:

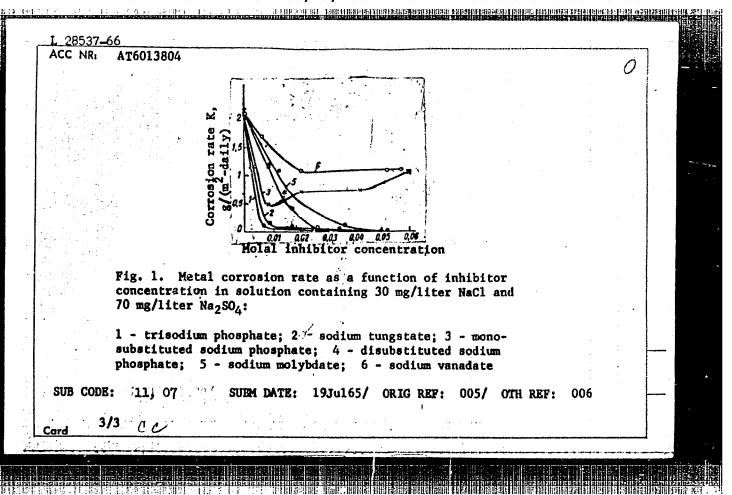
Na3PO4 = Na2HPO4 > Na2WO4 > Na2MOO4 > NaH2PO4 > Na2VO4.

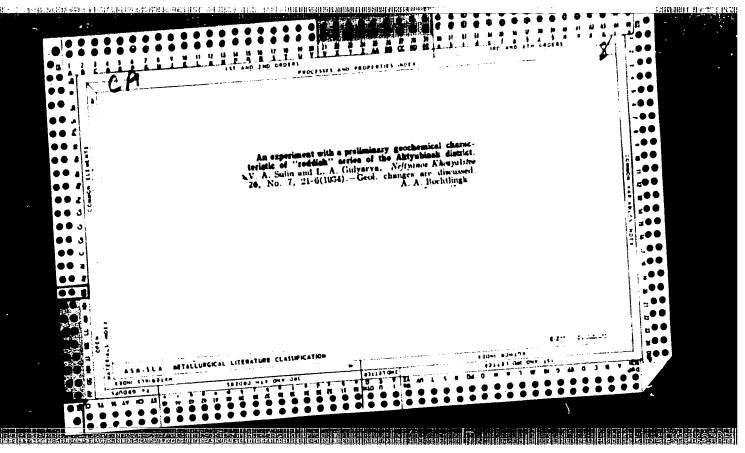
It is found that these inhibitors markedly alter impedance when the current applied is small, do not affect capacitance characteristics in the presence of high frequencies but somewhat reduce ohmic resistance at these frequencies. Such changes in impedance indicate that inhibitors of this type (XO_4^{R}) alter the polarization characteristics of the system. Orig. art. has: 9 figures.

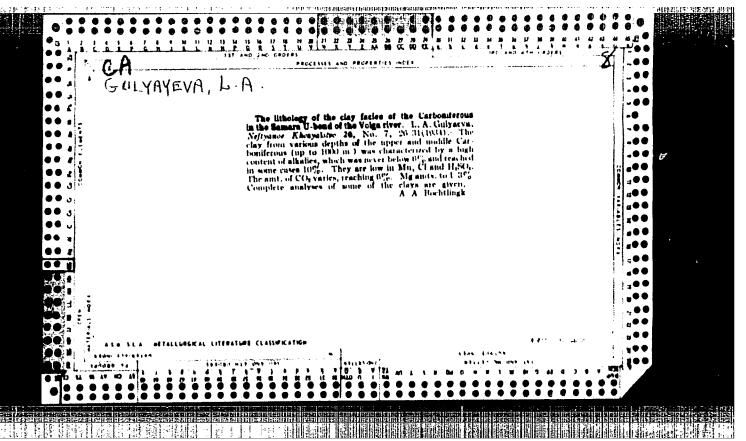
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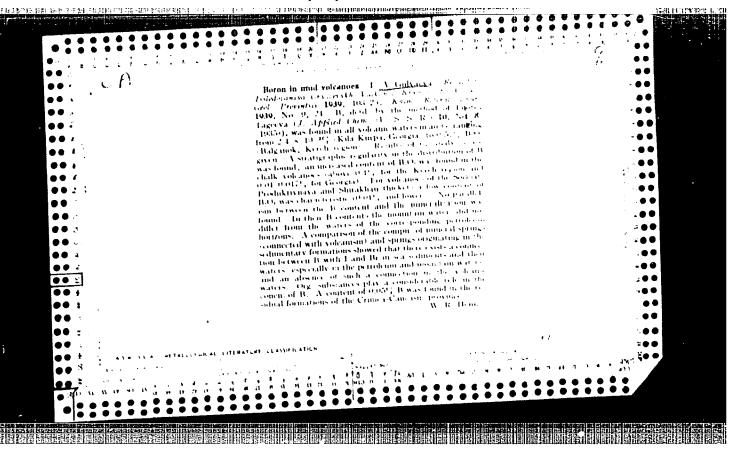
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GULYAYEVA, L. A.

"Vanadium, Nickel, and Copper in Petroleum of the Urals and Volga Region" Dox
AN, 32, No. 6, 1941. Inst. Mineral Fuels, Acad Sci, USSR.

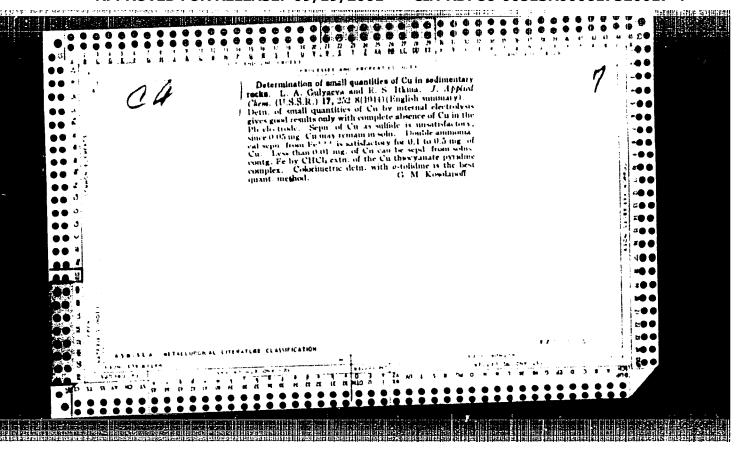
GULYAYEVA, L. A.

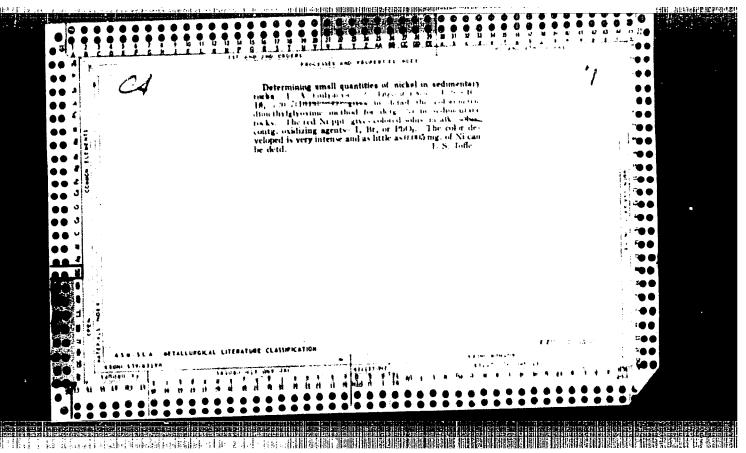
"Disbribution of Boron in the Waters of Azerbaydzhan Oil-Fields and its Correlational Value, Dok. AN, 35, No. 3, 1942.

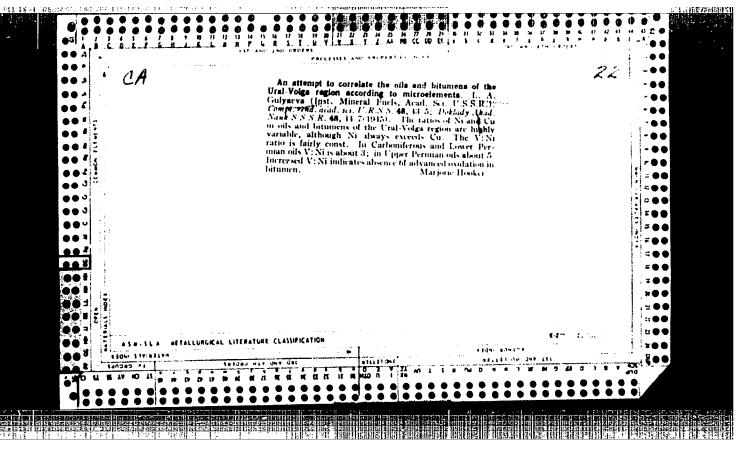
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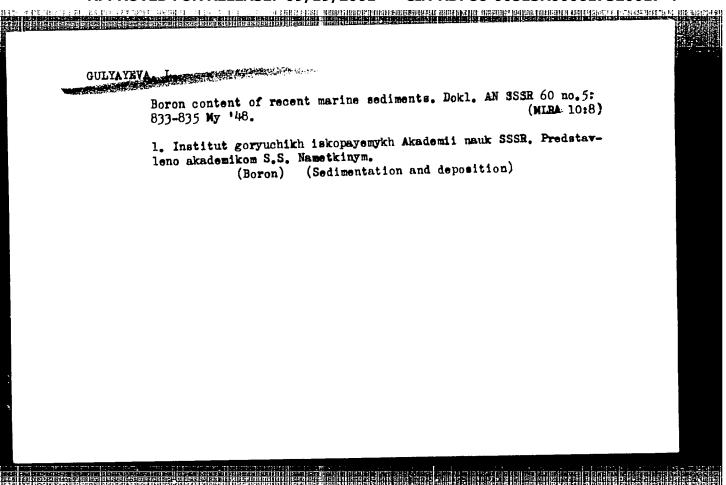
GULYAYAYA, L. A.

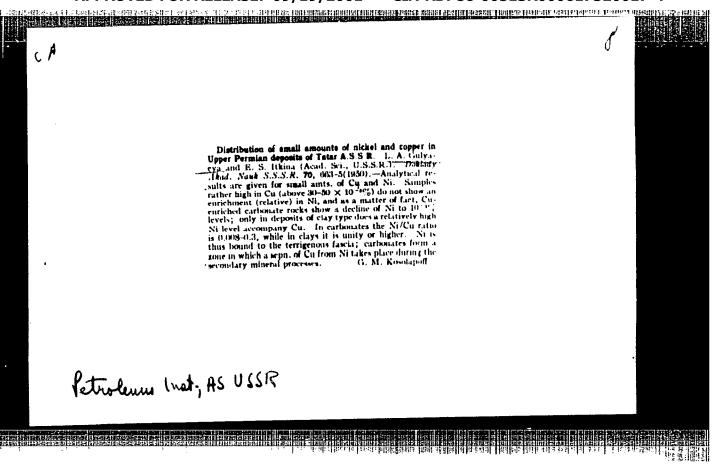
"Boron Distribution in Recent Organogenic Deposits," Dok AN. 37, No. 1, 1942.

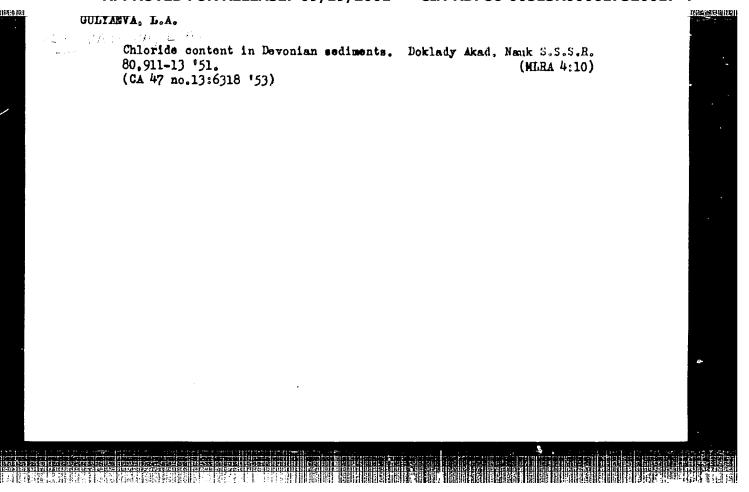


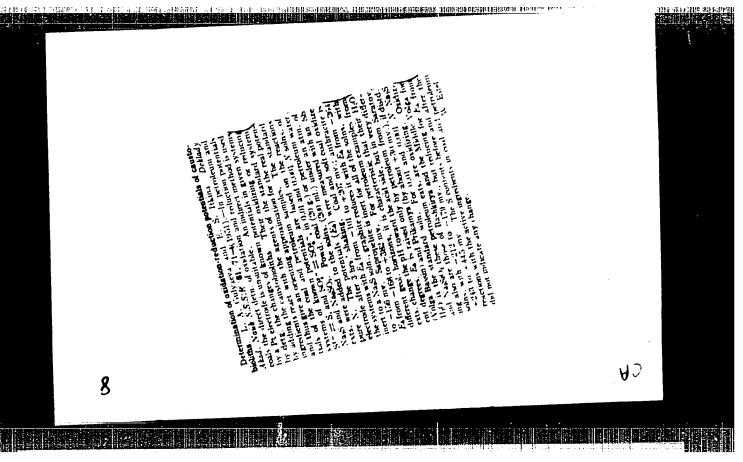




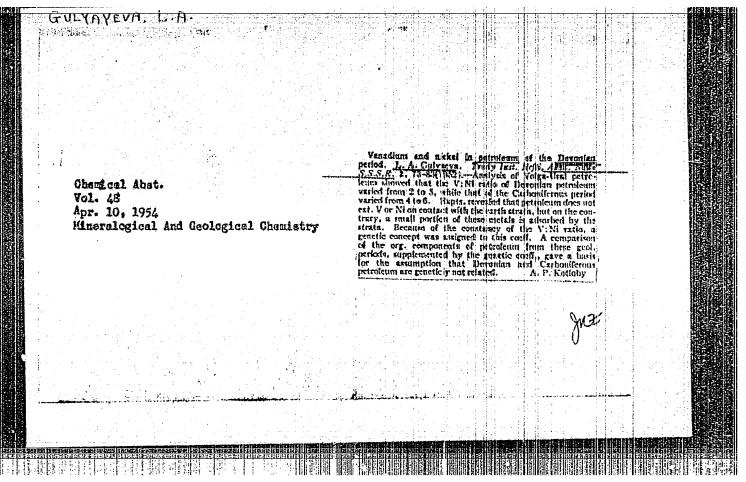


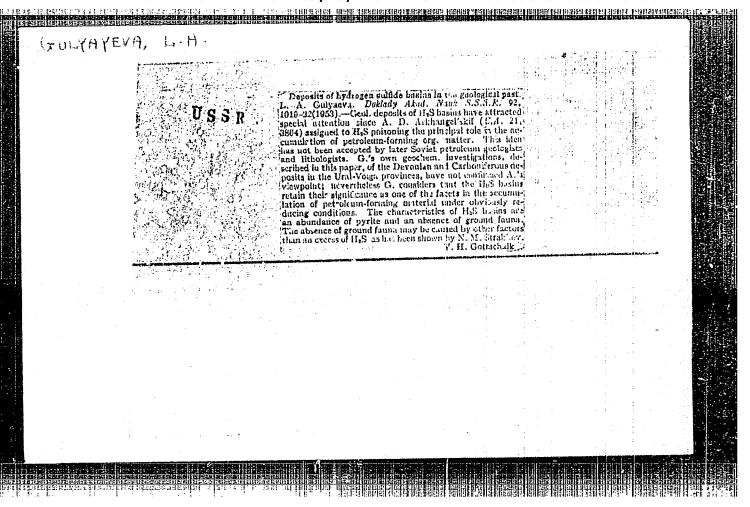






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Colyayeva, L.A. -- "Geochemistr, of Terrigenous Deposits of the Devonian Period in the Urals Along the Volga." Dr Geol-Min Sci, Petroleum Inst, Acad Sci toom, 26 Jan 54.

(VECHEMINIATA EOSKVA, 19 Jan 54)

Source: SUM 168, 22 July 1954

